

Extending photoelectron spectroscopy into the bulk using Hard X-rays (HAXPES)

Ben F Spencer

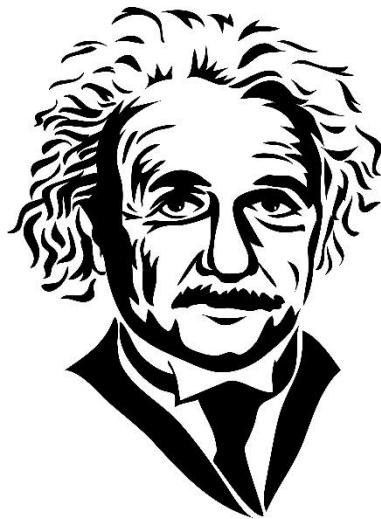
Department of Materials, University of Manchester
Sir Henry Royce Institute for Advanced Materials

19/02/2020



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Photoelectron spectroscopy

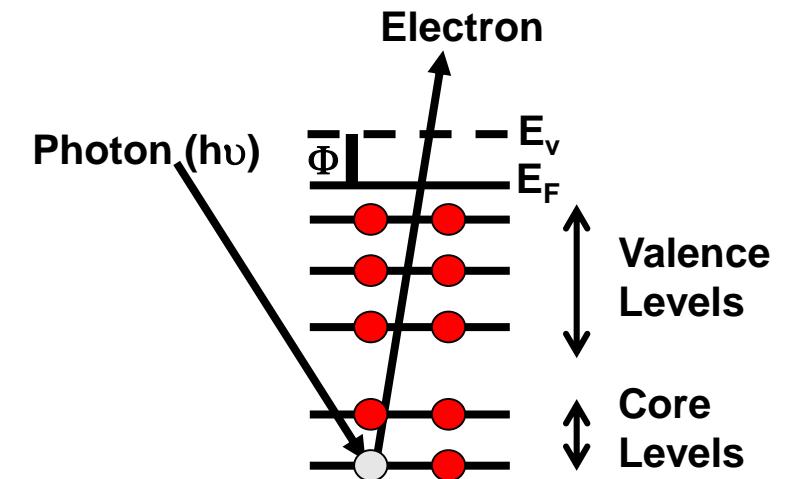
$$E_{KE} = h\nu - E_b - \Phi$$

E_{KE} - kinetic energy (measured)

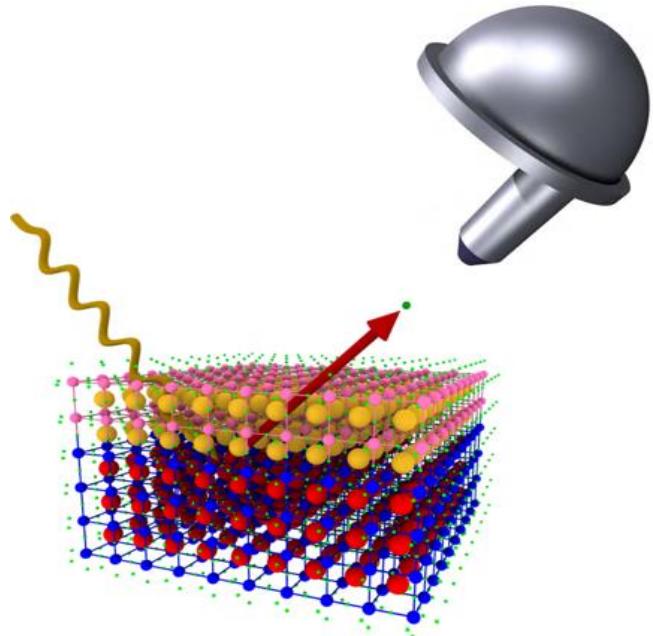
$h\nu$ - photon energy (known)

E_b - binding energy of photoelectron

Φ - work function (known)

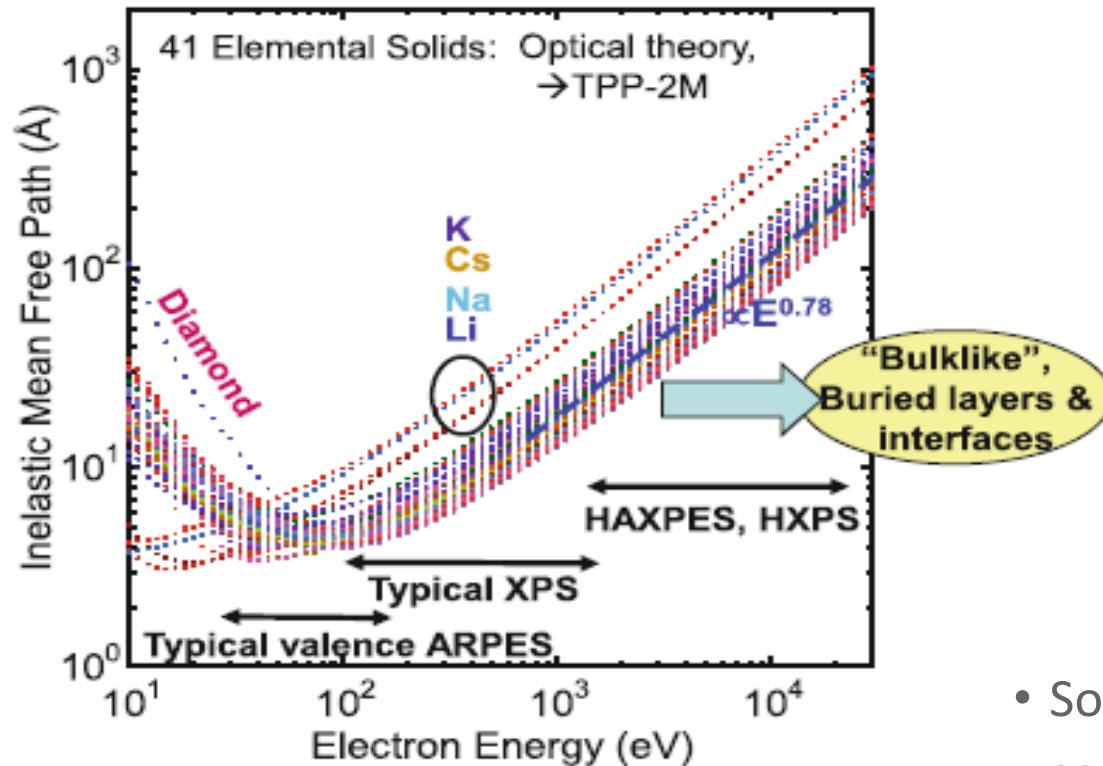


- The basis of chemical analysis using X-ray photoelectron spectroscopy (XPS)
- Used ubiquitously

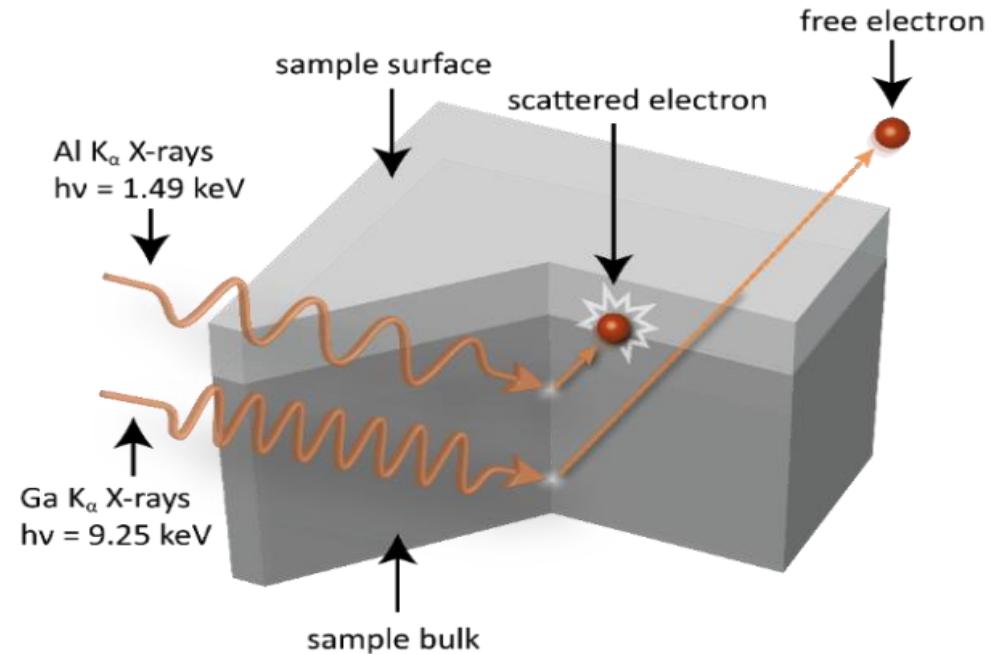


- BUT the electrons can only escape from the top surface layers
- So the sampling depth is only a few nm

Hard X-ray Photoelectron Spectroscopy (HAXPES)

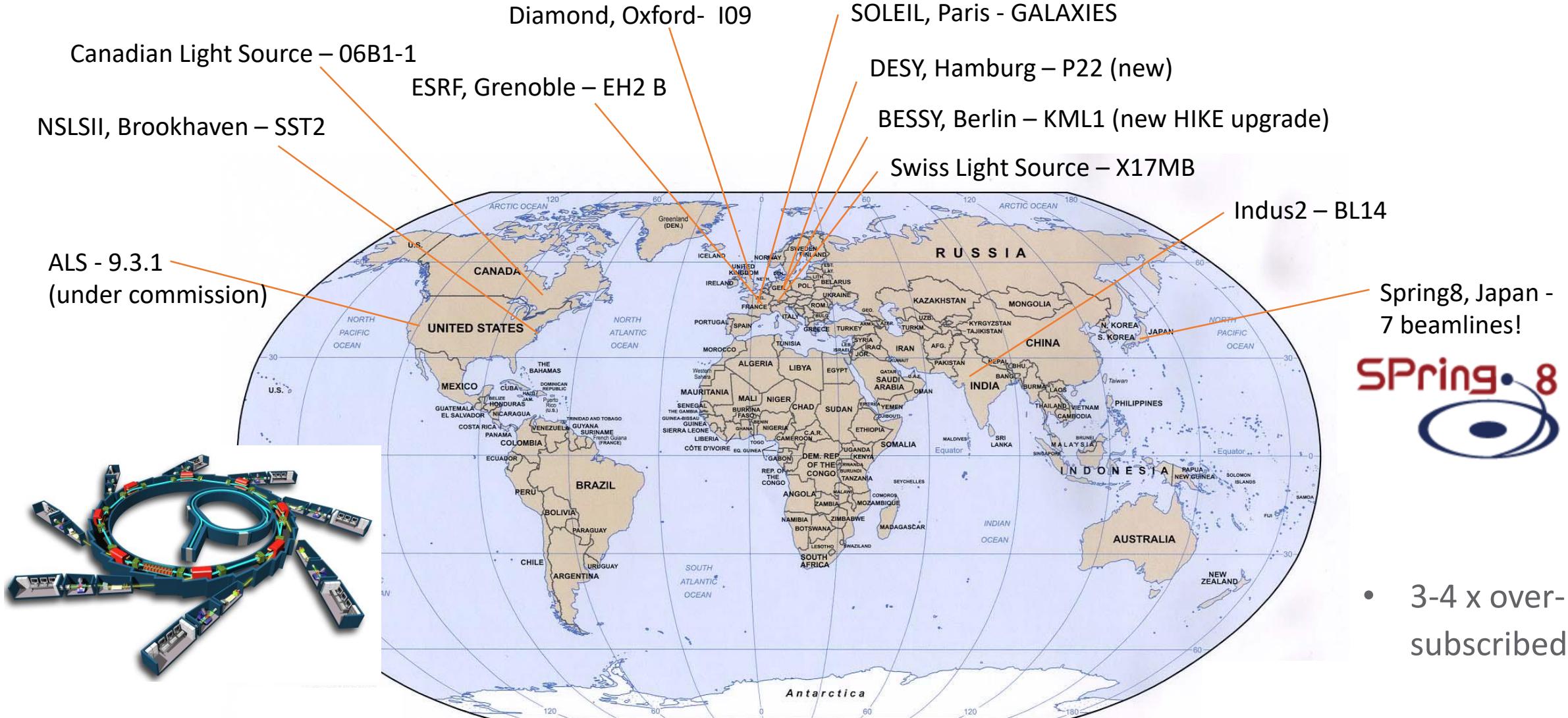


The Universal Curve of electron pathlength



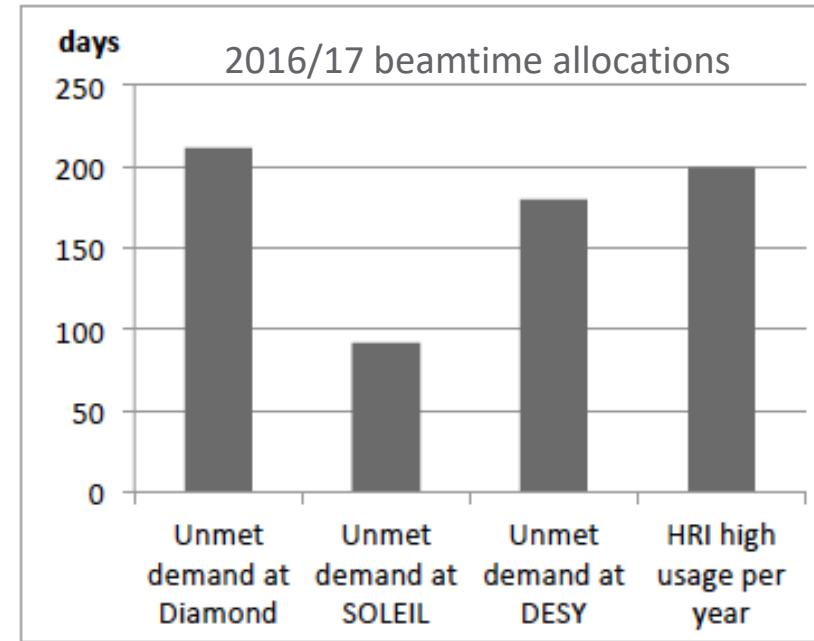
- So to probe deeper, we just use a harder X-ray source, right?
- Yes, but photoionisation cross sections plummet!
- Need a very high intensity source.

HAXPES facilities at world synchrotron sources



International unmet demand

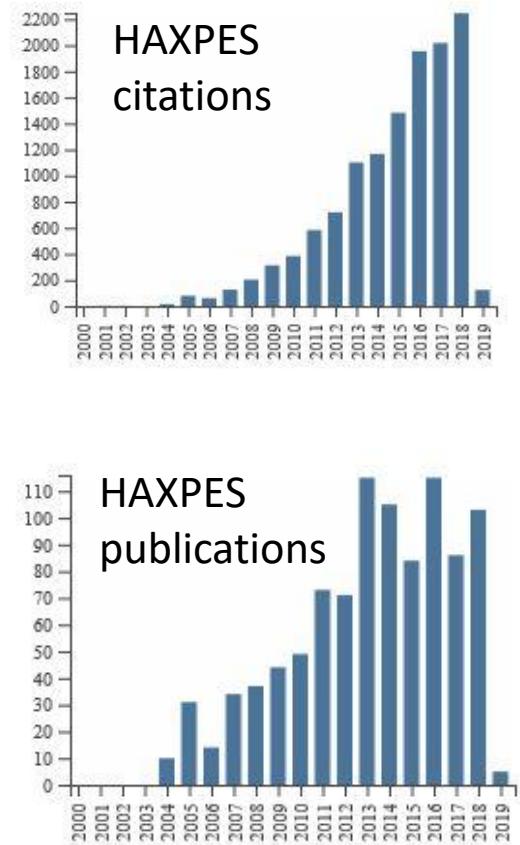
- The oversubscription of international facilities has led to saturation in the amount of work that can be carried out, but the impact of HAXPES continues to rise.



- Urgent need to develop high intensity lab-based sources

- Underprovision recognised in EPSRC roadmap (2017):

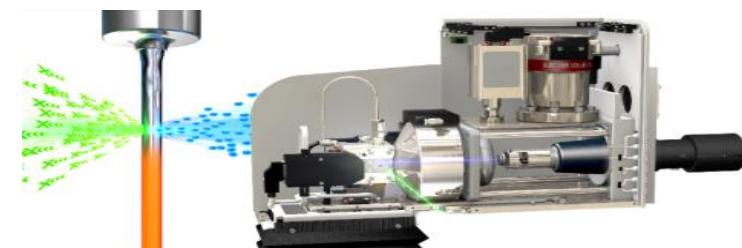
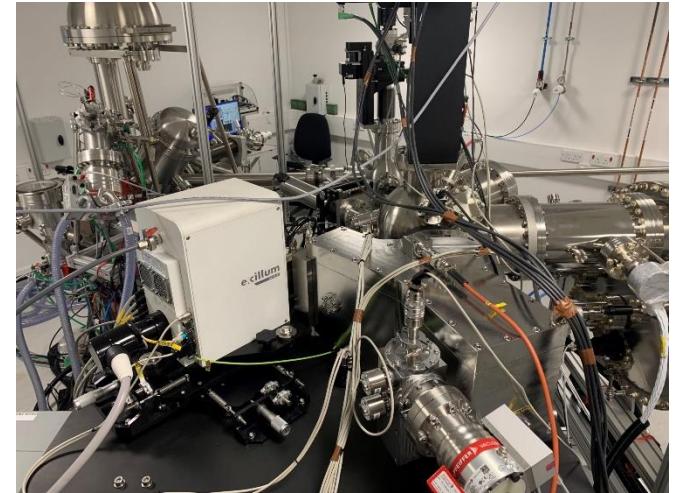
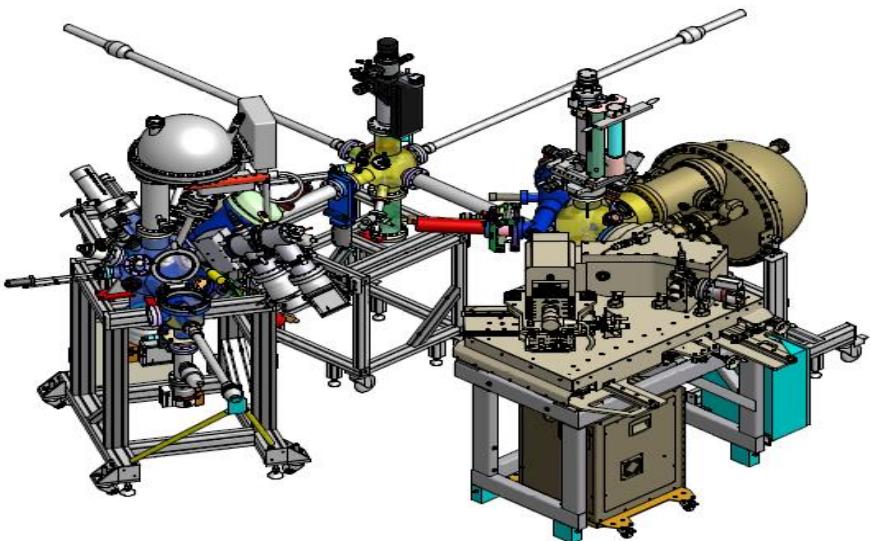
<http://www.epsrc.ac.uk/files/research/roadmap-for-photoelectron-spectroscopy/>



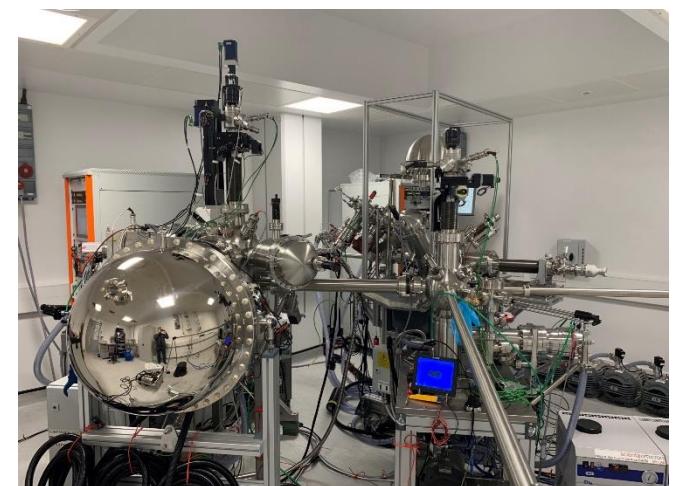
Hard X-ray Photoelectron Spectroscopy (HAXPES) at HRI

scientaOMICRON

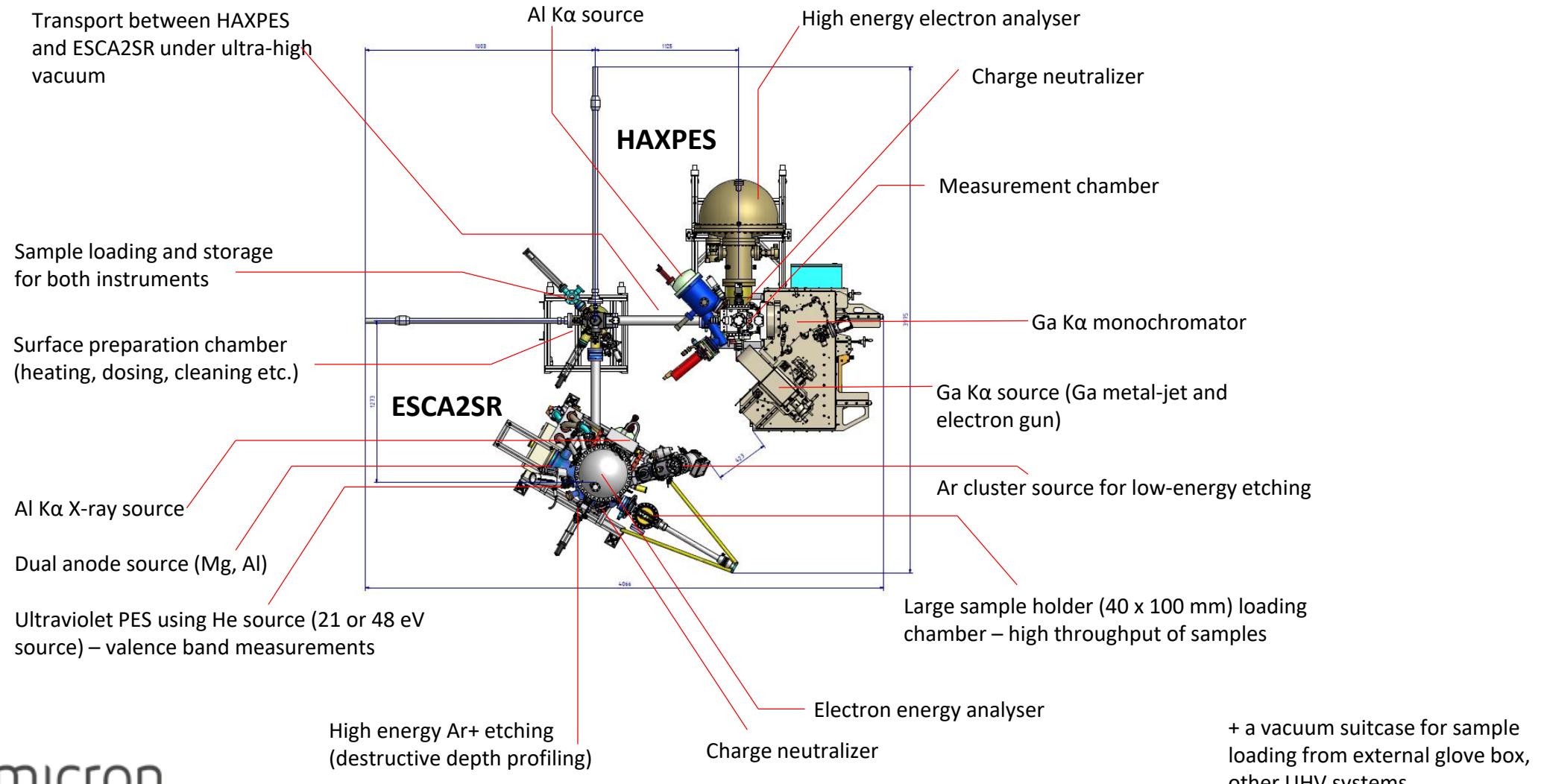
- three orders of magnitude increase in X-ray intensity
- 50 μm spot size
- X-ray photon energy 9.25 keV (Excillum Ga metal jet)
- High throughput, high kinetic energy electron analyser (EW4000)



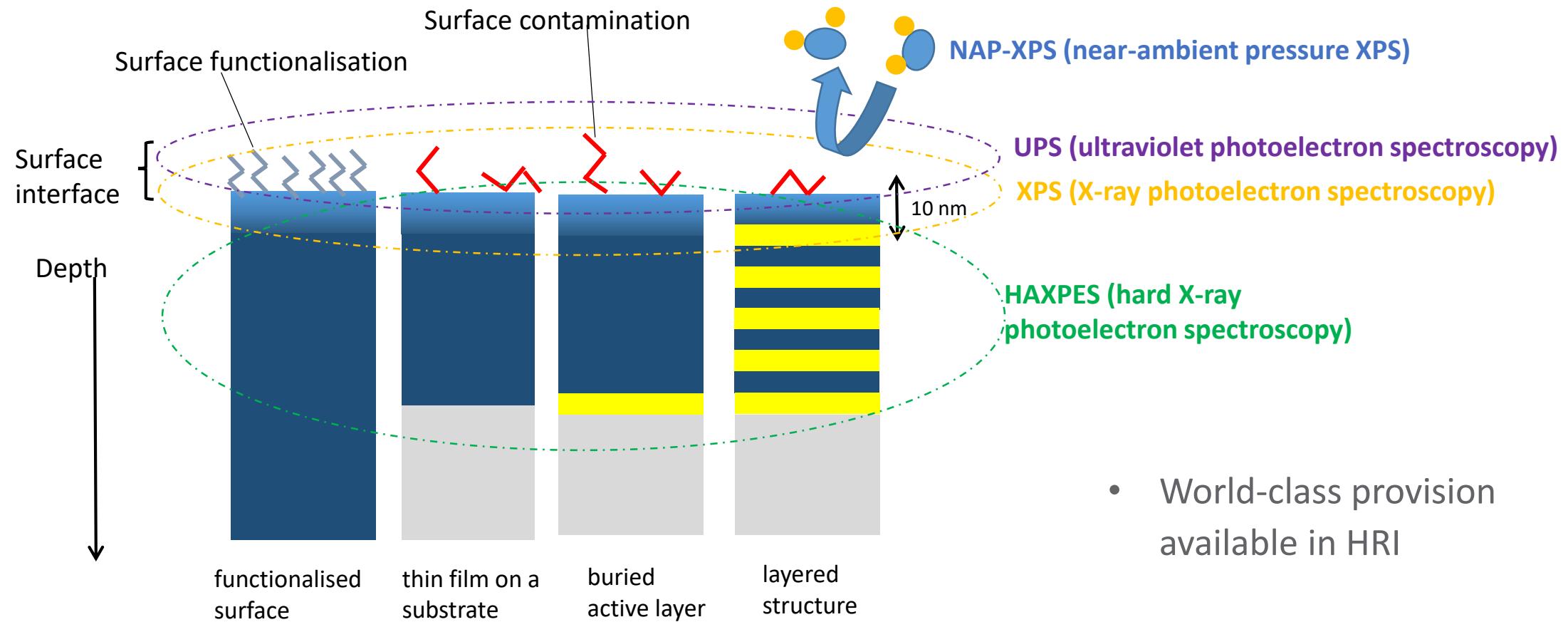
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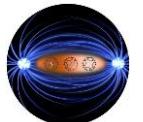
Combined HAXPES and XPS at HRI



Chemical state profiling from the surface to the bulk



HAXPES in the Royce- supporting themes



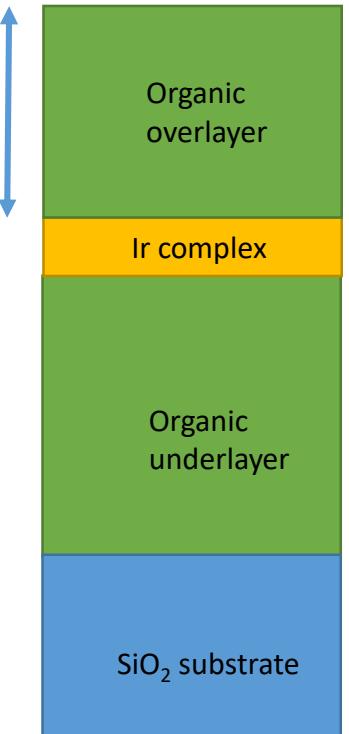
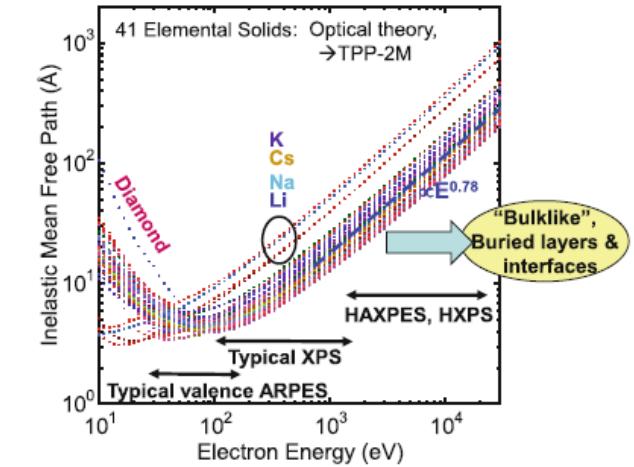
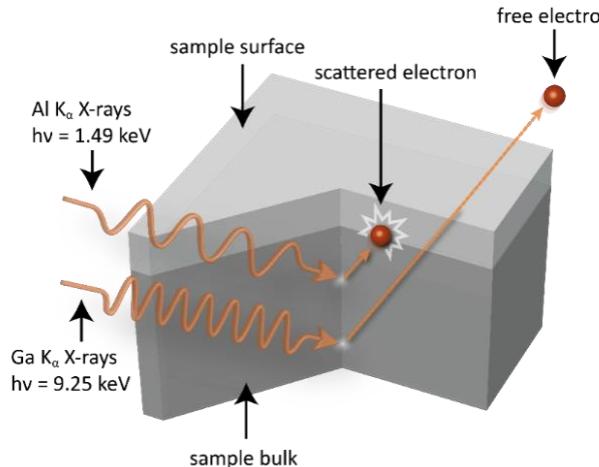
- *Atoms to devices*: locate buried interfaces in semiconductor heterostructures
- *Biomedical materials*: measure light elements (C,N) in prototype medical devices without damage
- *Energy storage*: characterise buried interfaces in working batteries, understand the solid-electrolyte interface
- *Materials systems for demanding environments*: understand corrosion scales from surface to bulk
- *Nuclear materials*: safely & non-destructively measure corrosion and contamination; contribute to whole-life management of materials
- *2D materials*: obtain layer-by-layer information from van der Waals heterostructures and nm-scale devices



Materials for Energy Efficient ICT: buried interfaces, layered structures, thin coatings, bulk chemical environment

Establishing lab-based HAXPES @ 9.25 keV now requires:

- Sensitivity factors – quantification
- Detection limits
- Analysis protocols
- Use of inelastic background modelling for depth profiling beyond the elastic limit
- Standardisation, incl compare lab system to synchrotron data



Test using a model system -- Ir-complex (green emitter in organic-LED displays) buried under organic

- Prepared at NPL - high quality, with precision layer thicknesses
- Due to be part of an upcoming BIPM (International Bureau of Weights and Measures) study to establish accuracy in the measurement of buried organic layers

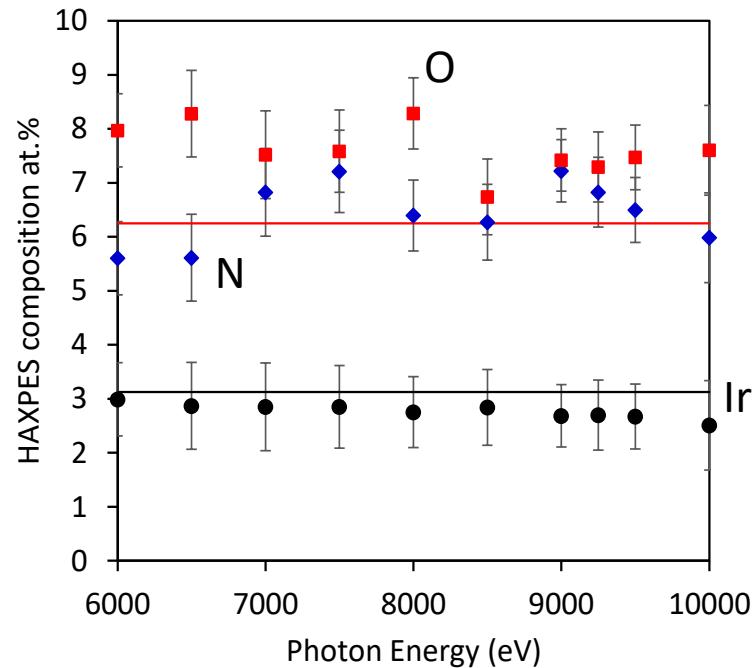
A G Shard *et al.*, Analytical Chemistry **84** 7865 (2012)

Sensitivity factors

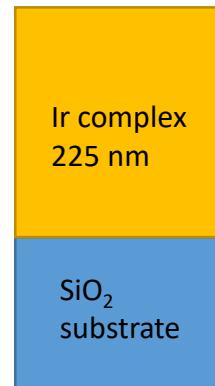
$$X_A = 100\% \times \frac{A_A/I_A}{\sum_i A_i/I_i}$$

$$I \propto J_{h\nu} T_E \lambda \frac{\sigma}{4\pi} (1 + \beta)$$

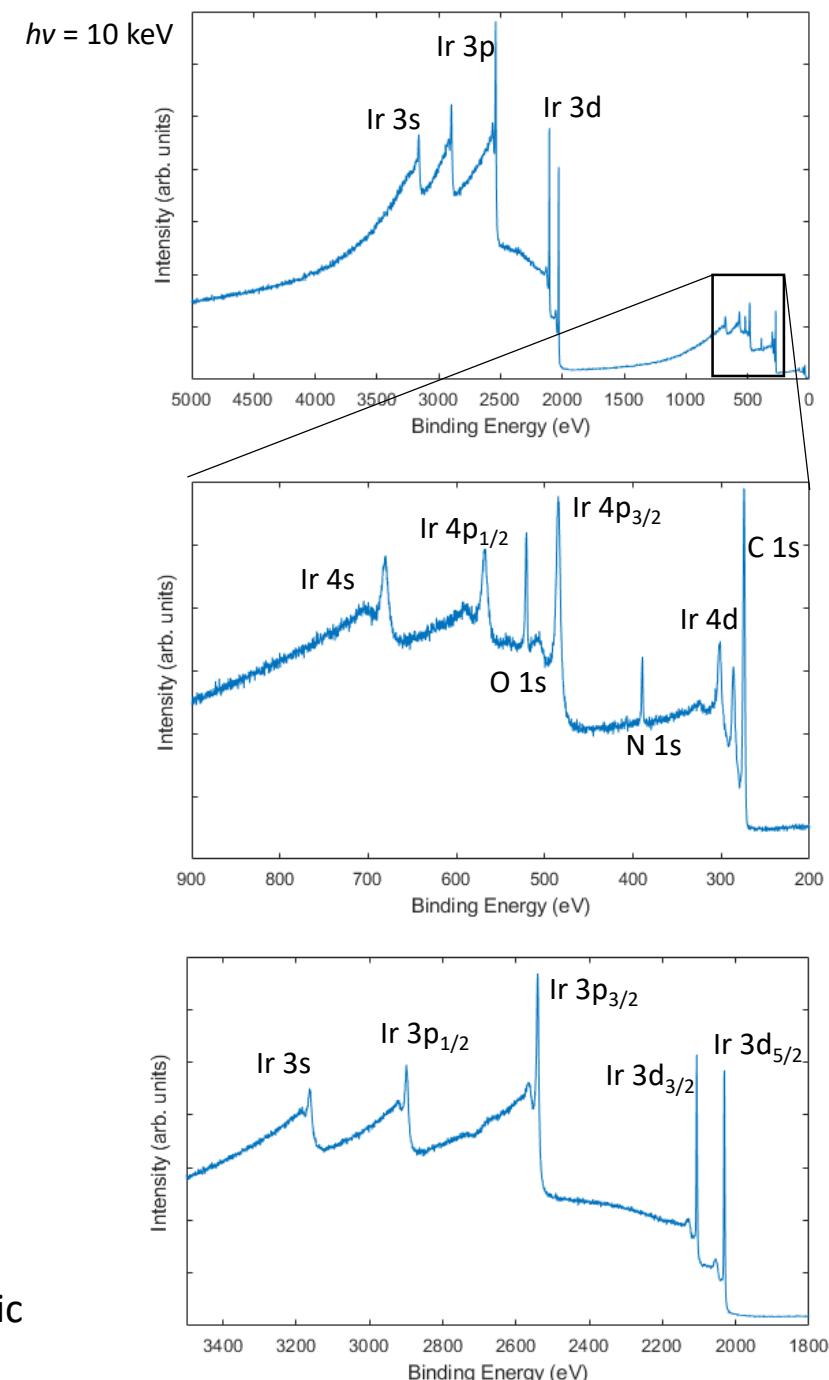
$$I_A = \lambda_A \sigma_A (1 + \beta_A)$$



Consistent for $h\nu = 6, 7, 8, 9, 10$ keV
Consistent using Ir 3s through 4d.



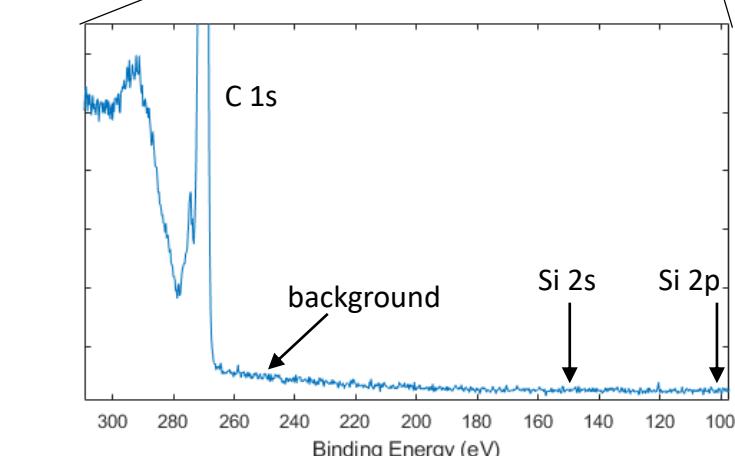
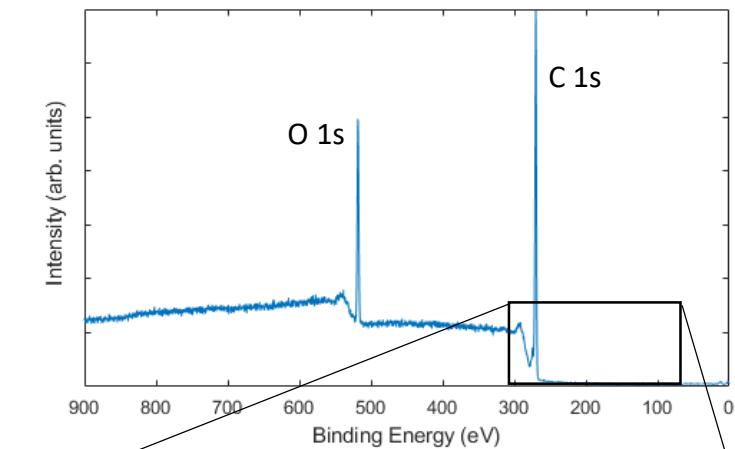
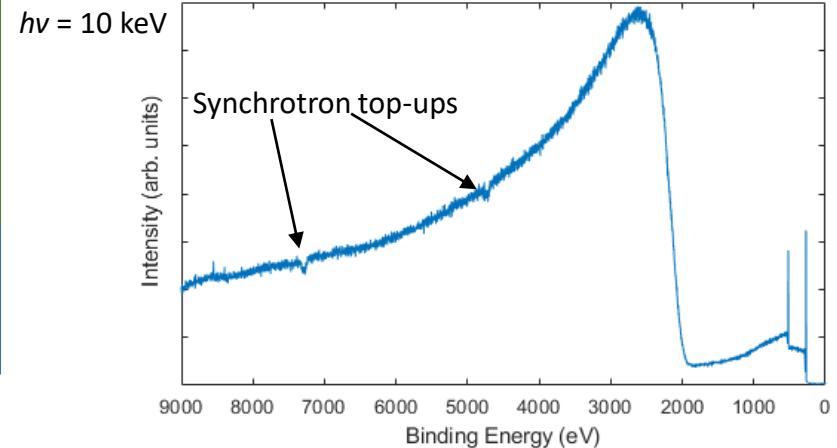
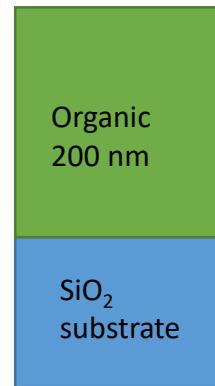
Reference sample – pure Ir complex
 $\text{Ir(ppy)}_2(\text{acac})$, $\text{C}_{27}\text{H}_{23}\text{IrN}_2\text{O}_2$



Reference sample – 200 nm organic underlayer on SiO_2

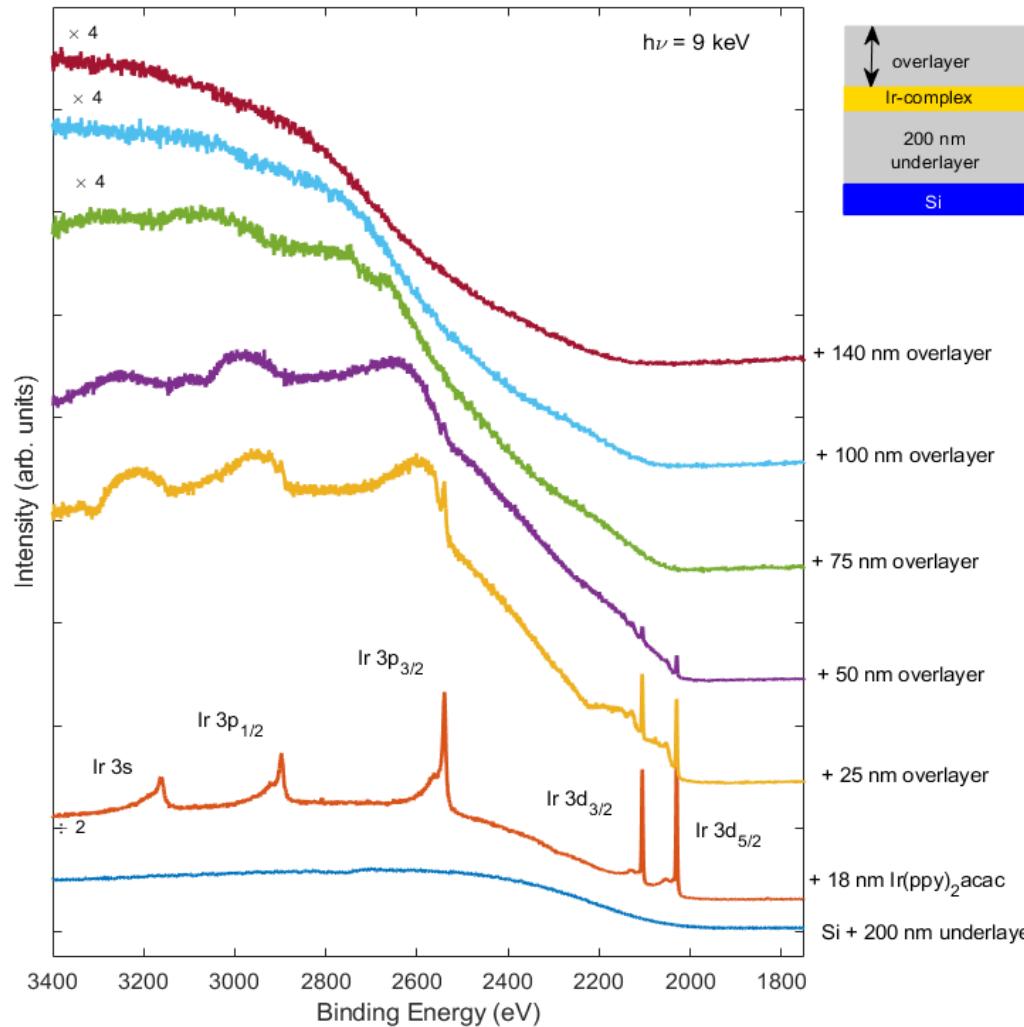
Irganox (1010) $\text{C}_{73}\text{H}_{108}\text{O}_{12}$

$h\nu$	Percentage	
	C	O
10000	85.72	14.28
9000	86.05	13.95
8000	85.14	14.86
7000	85.17	14.83
6000	84.90	15.10
Average	85.39	14.61
Expected	85.88	14.12



Inelastic background originating from the Si 1s core level already shows the potential for extracting depth information over >> 50 nm

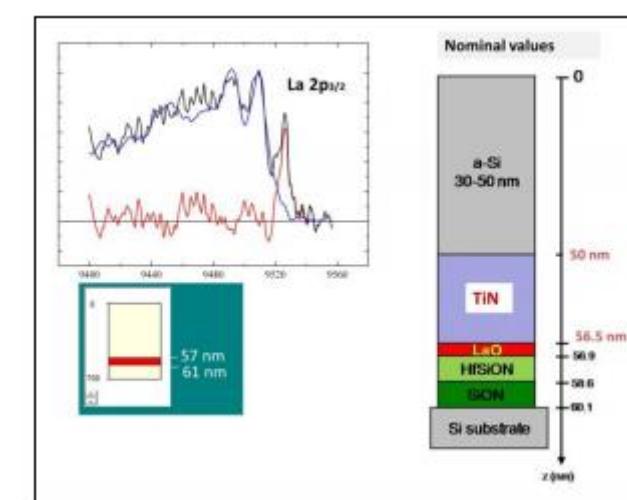
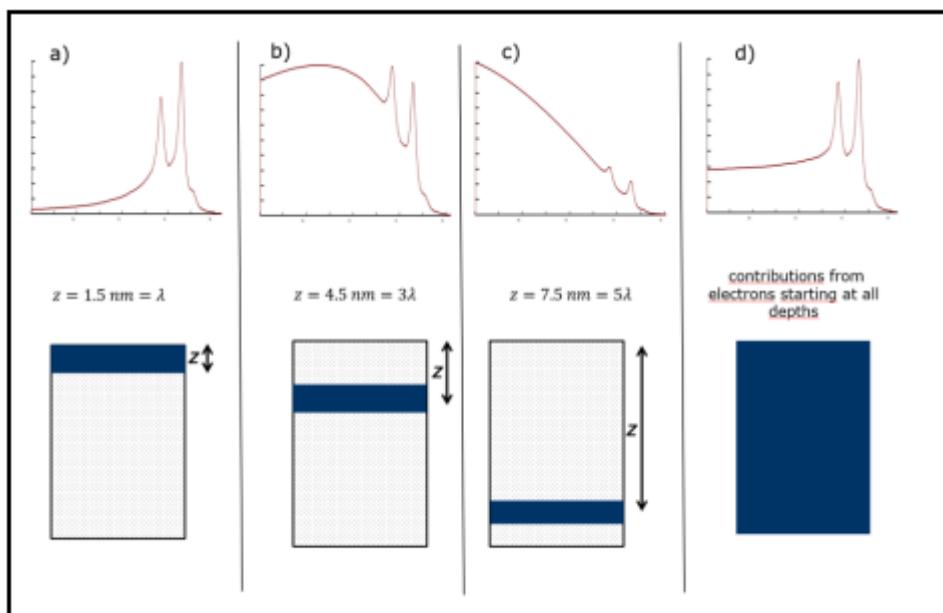
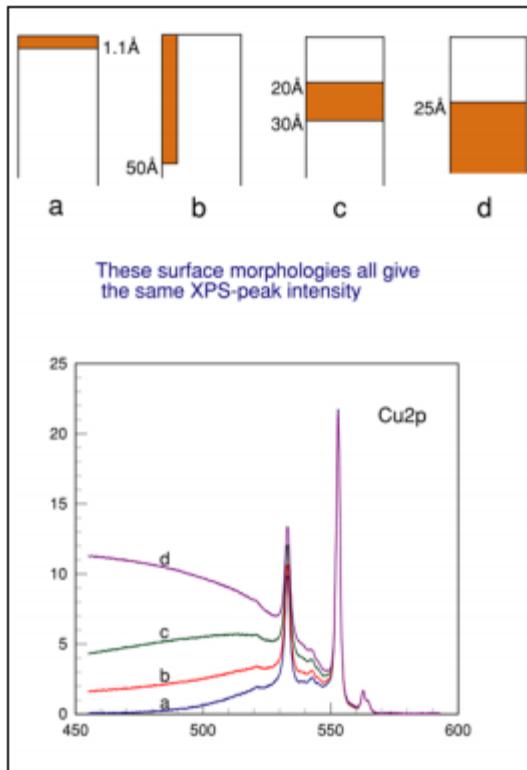
Calculation method can be extended to all elements; requires further testing



Inelastic background originating from each core level creates a distinctive “signature”

Core levels measured up to 50 nm overayers

Inelastic background Tougaard analysis



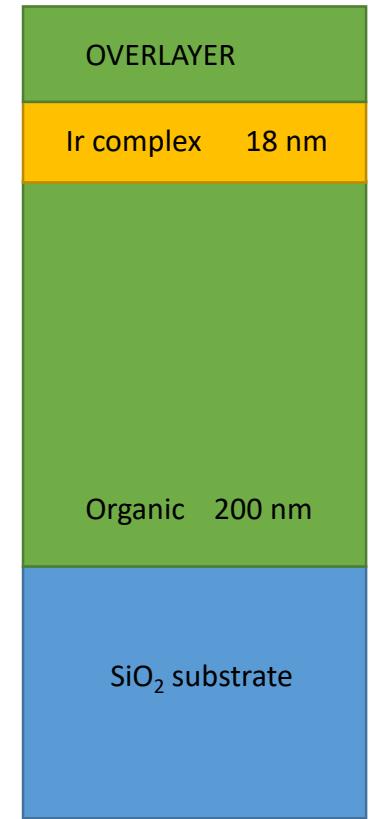
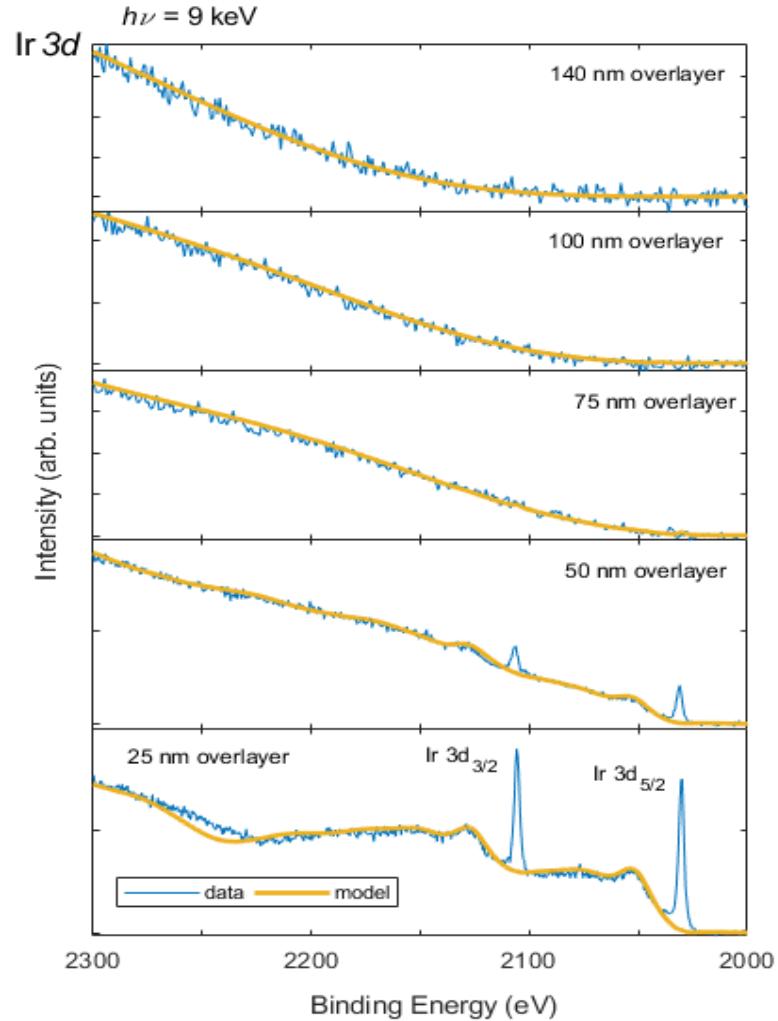
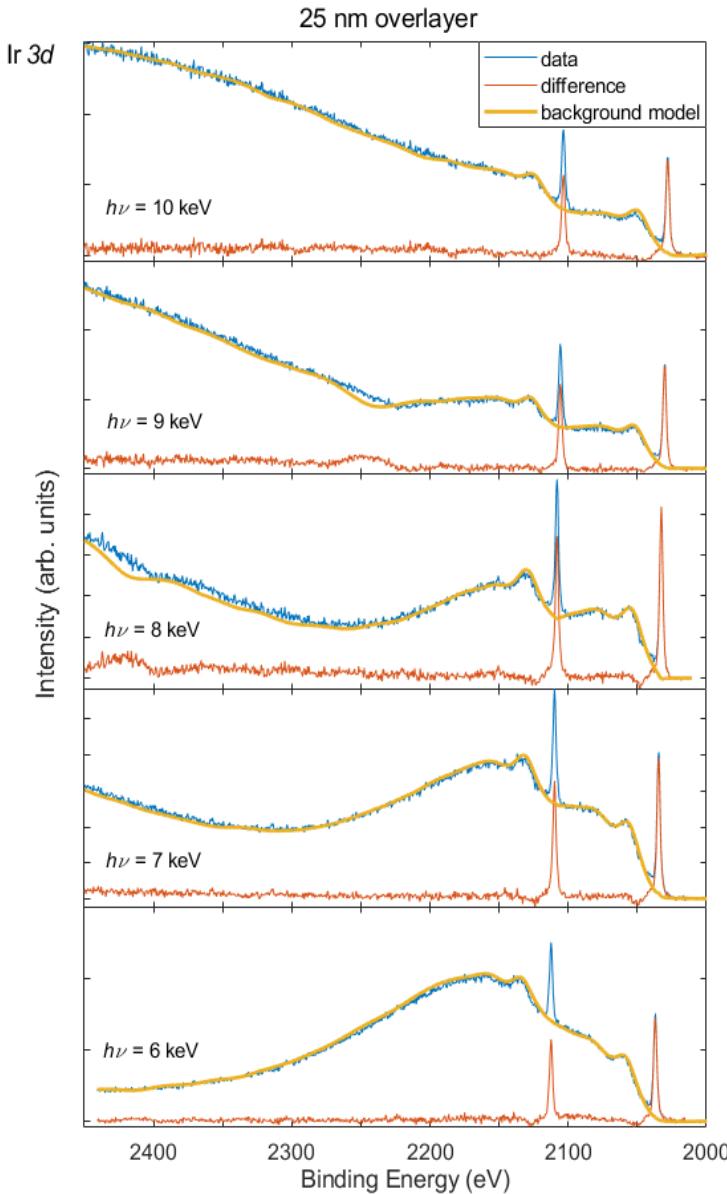
Enabled in QUASES software (www.quases.com)

- IMFP is a critical parameter
- Reference data important for layered structures
- Proposed that this enables information from depths $\sim 20 \times$ IMFP for HAXPES (spectra contain wider region of energy loss)

Y.-T. Cui *et al.*, J. Appl. Phys. **121** 225307 (2017)

S. Tougaard, Journal of Surface Analysis **24** 107 (2017)

S. Tougaard, Surf. and Inter. Anal. **11** 453 (1988)

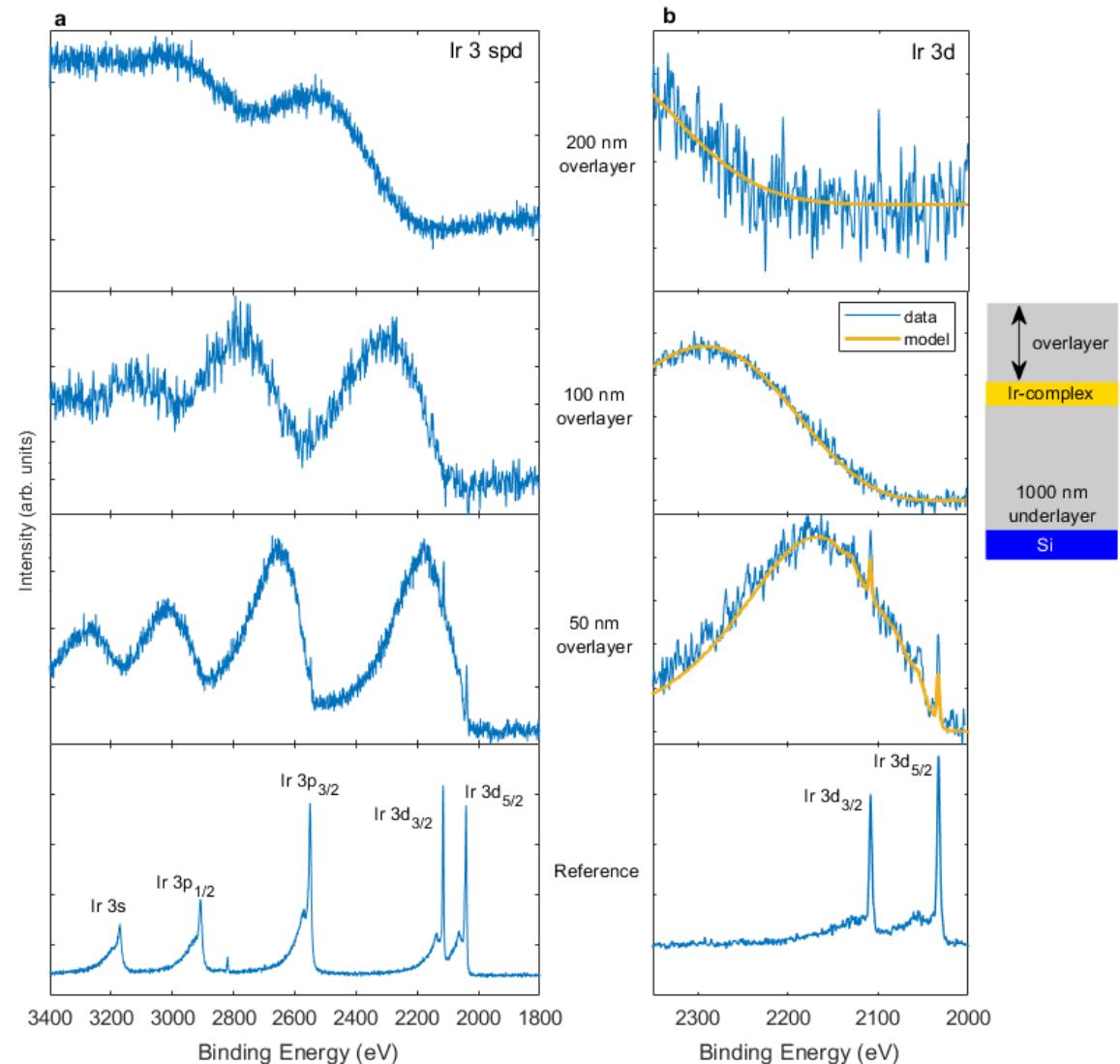
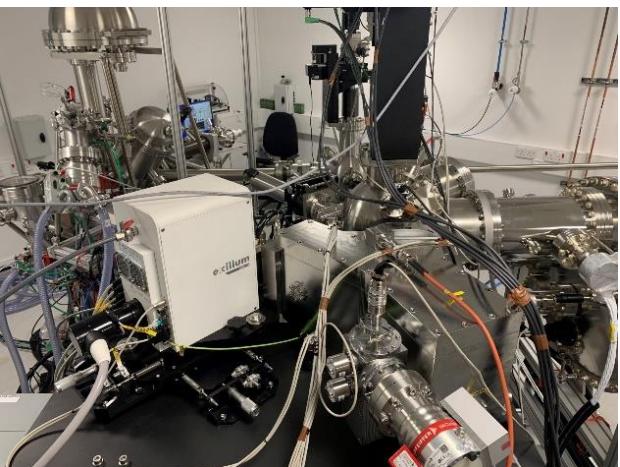
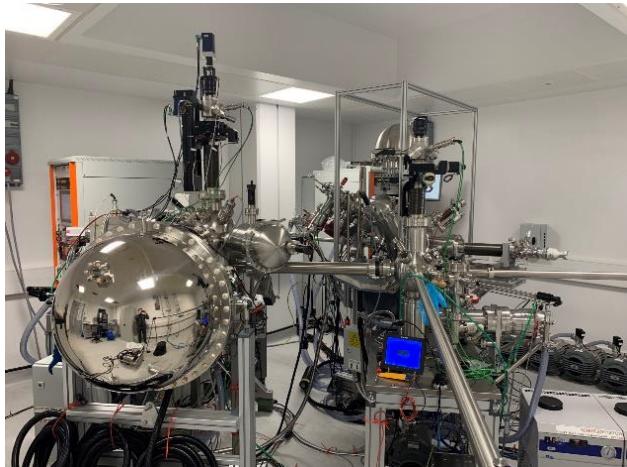


Overlayer thickness modelled with $\sim 5\%$ error
consistently for data using $h\nu = 6\text{-}10 \text{ keV}$

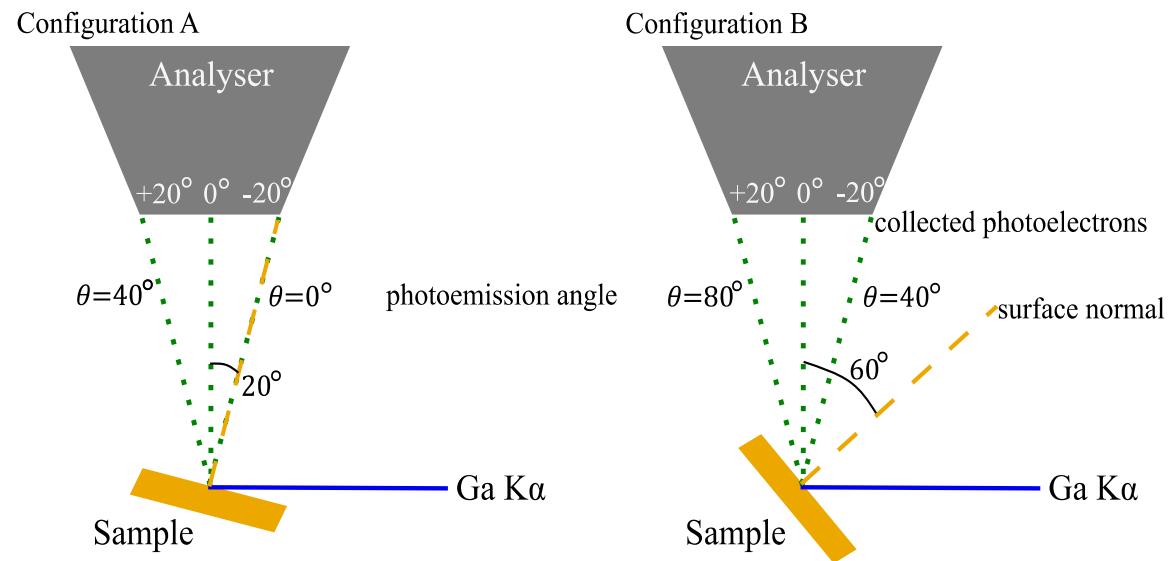
Lab-based HAXPES @ 9.25 keV

So much less flux- but so much more time!

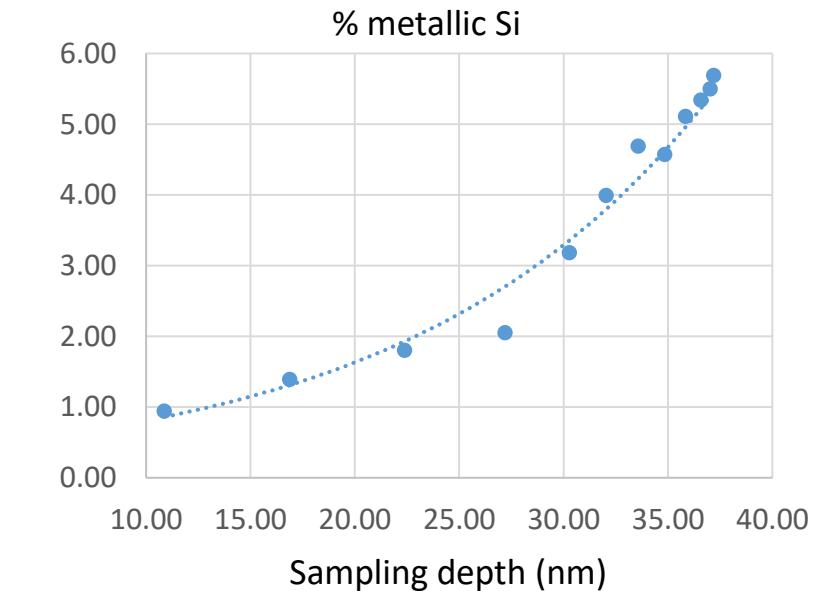
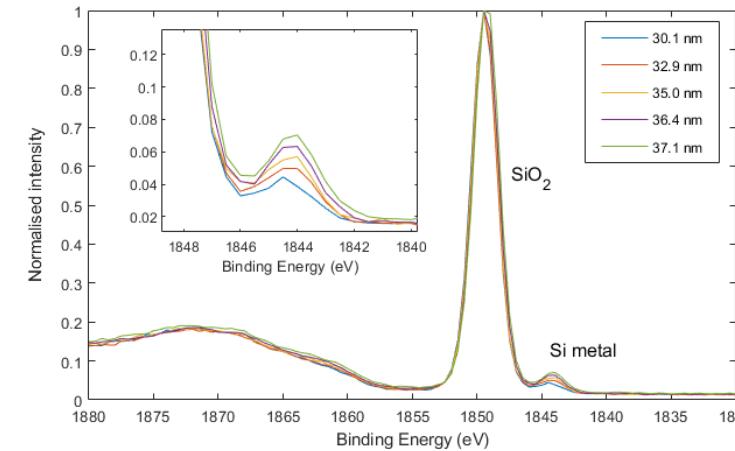
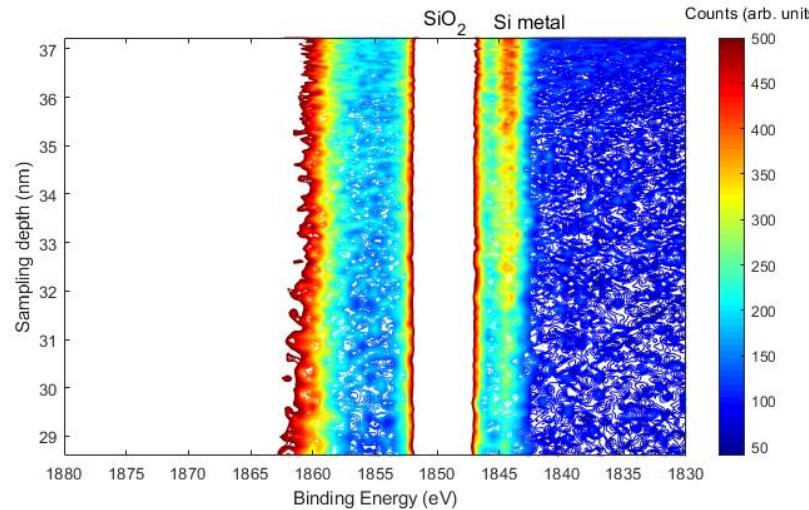
Can measure insulators using a neutraliser



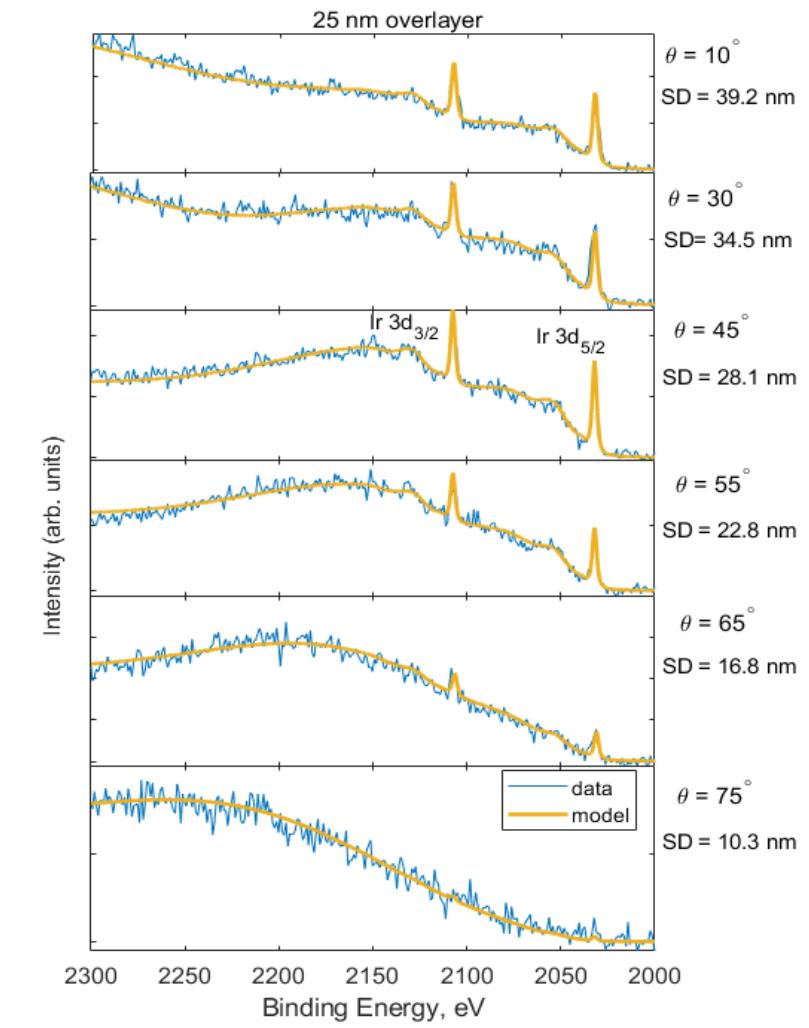
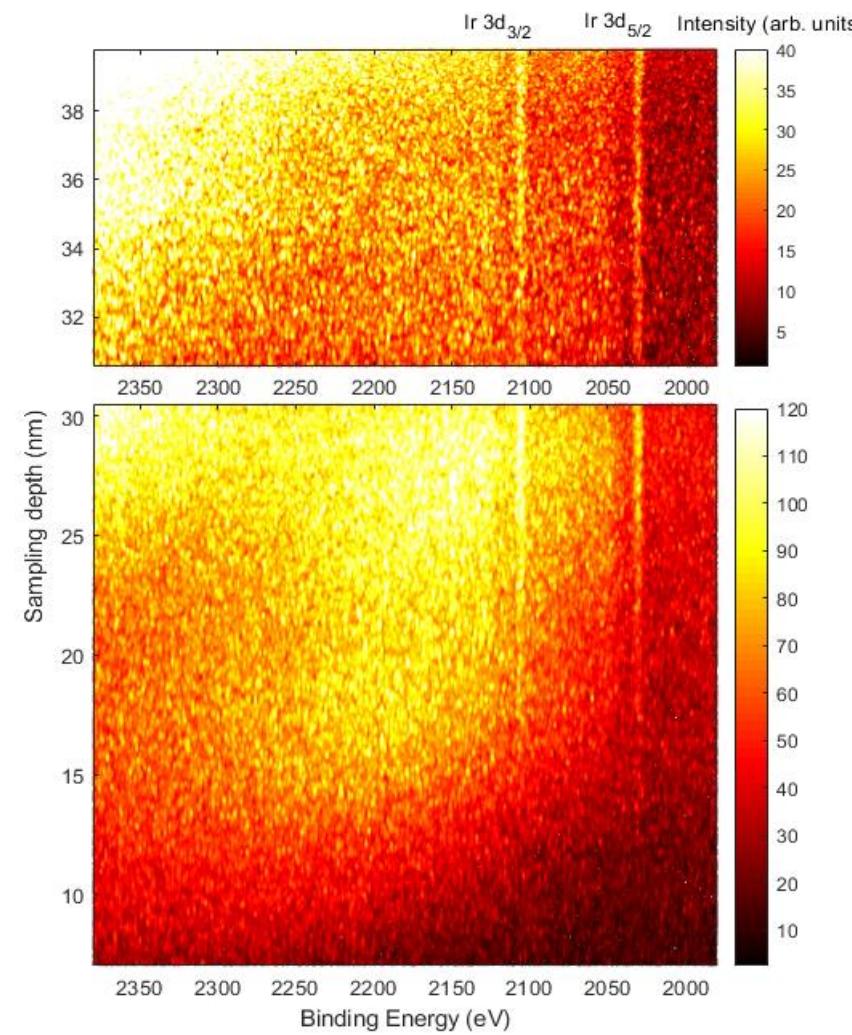
Use analyser in angle-resolved mode for depth profiling



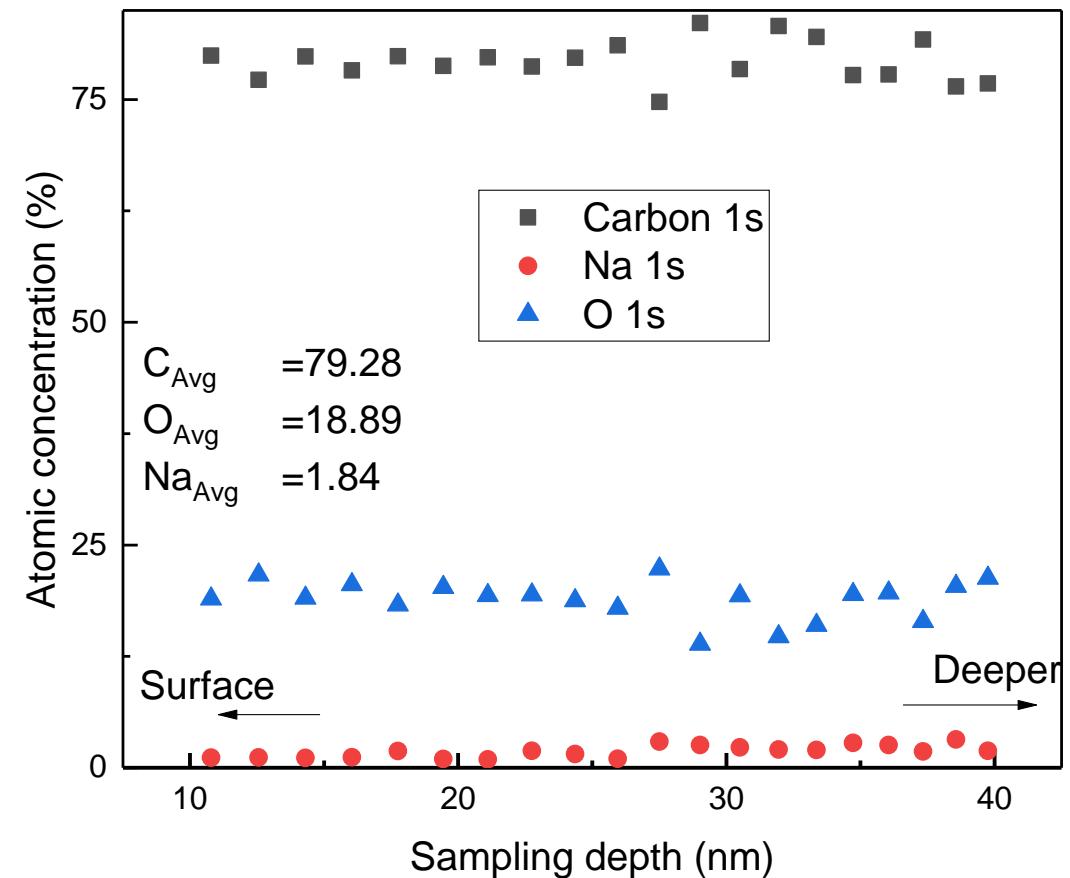
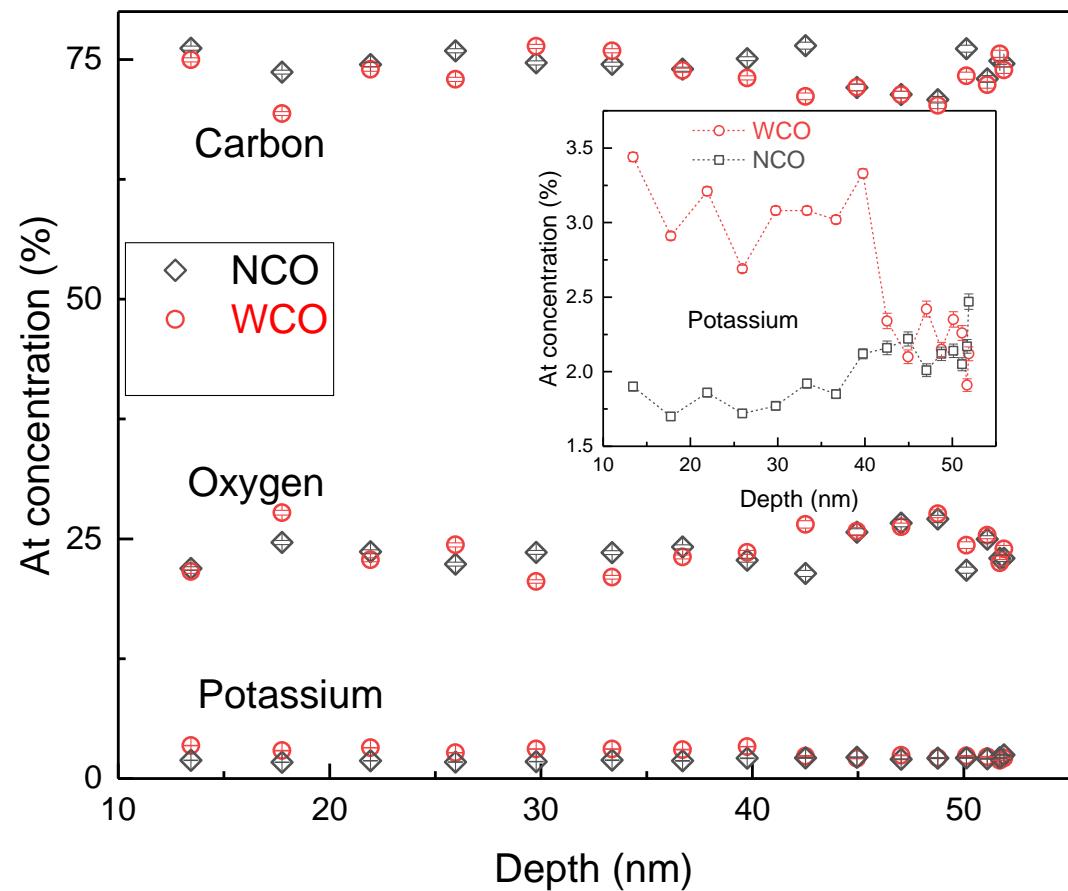
Si 1s – Si substrate with SiO_2 overlayer



Use analyser in angle-resolved mode for depth profiling

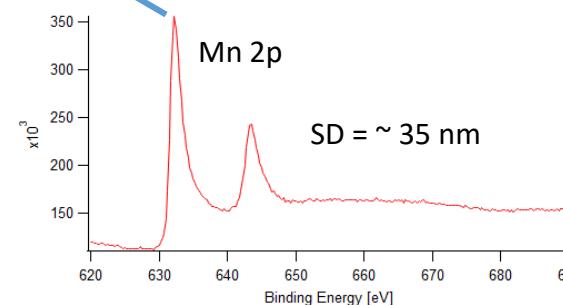
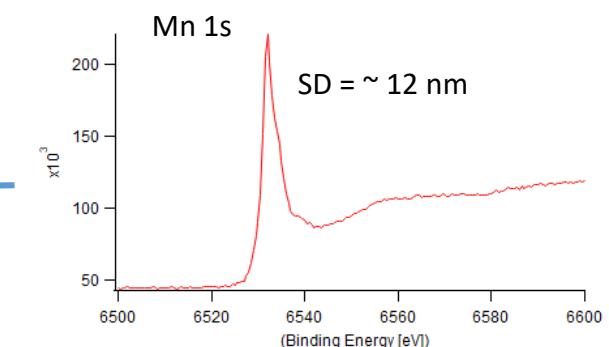
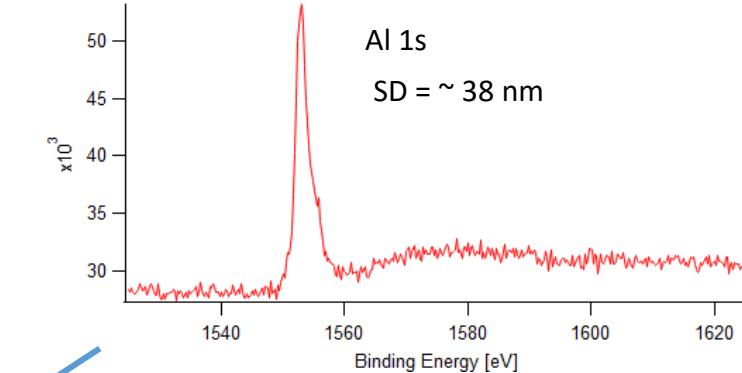
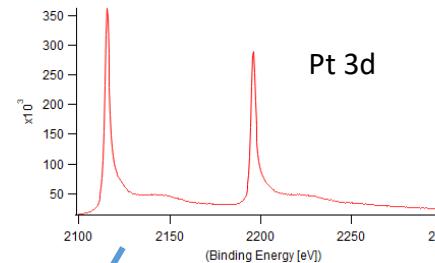
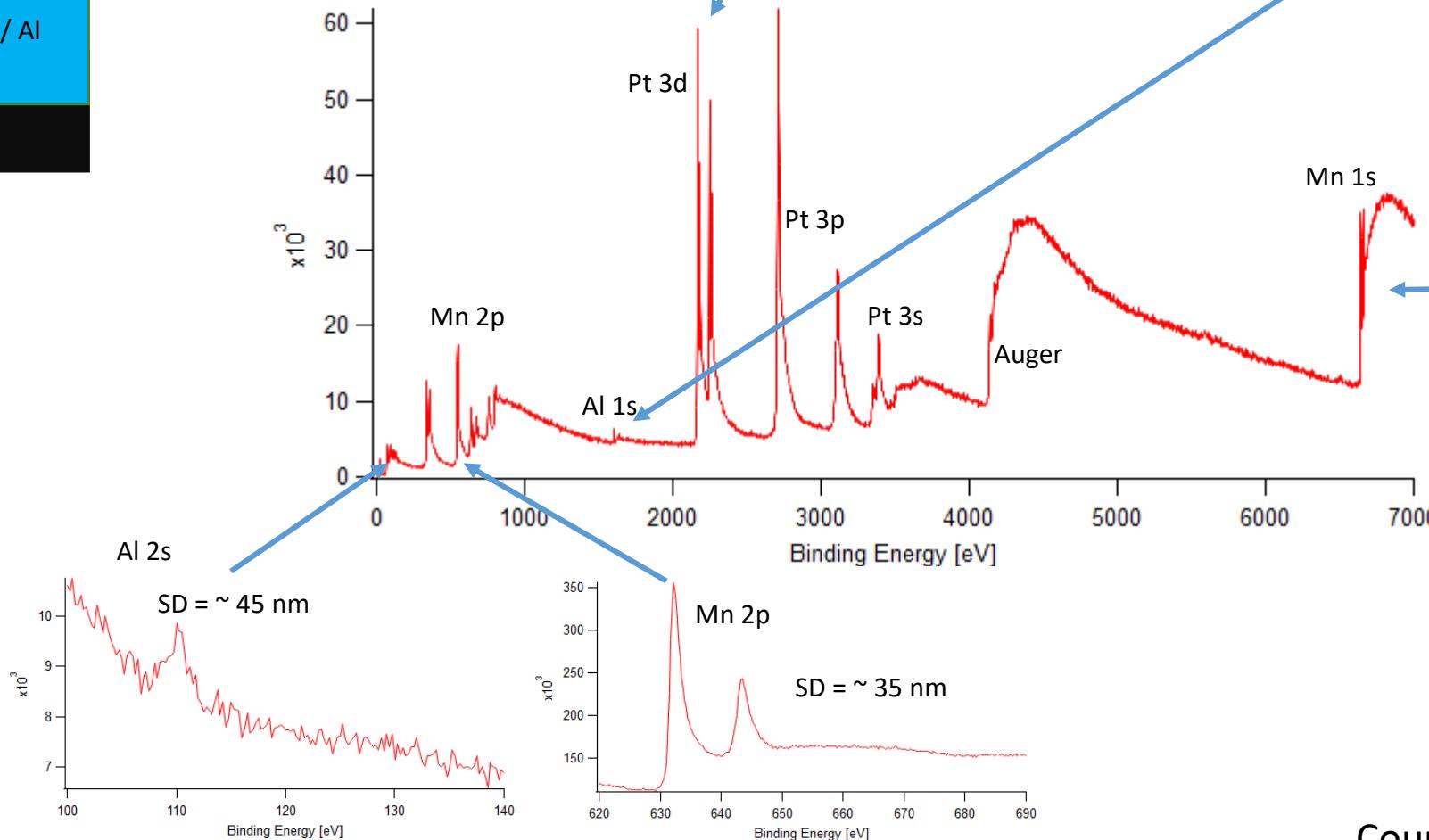


Trapping of ions in graphene oxide films



Courtesy: Prem Pillai, Rahul Nair

Heavier atoms –
multiple core levels =
multiple depths



Courtesy: Philip Thompson, Tom Thomson

What Lies Beneath? In situ and operando characterisation of battery materials

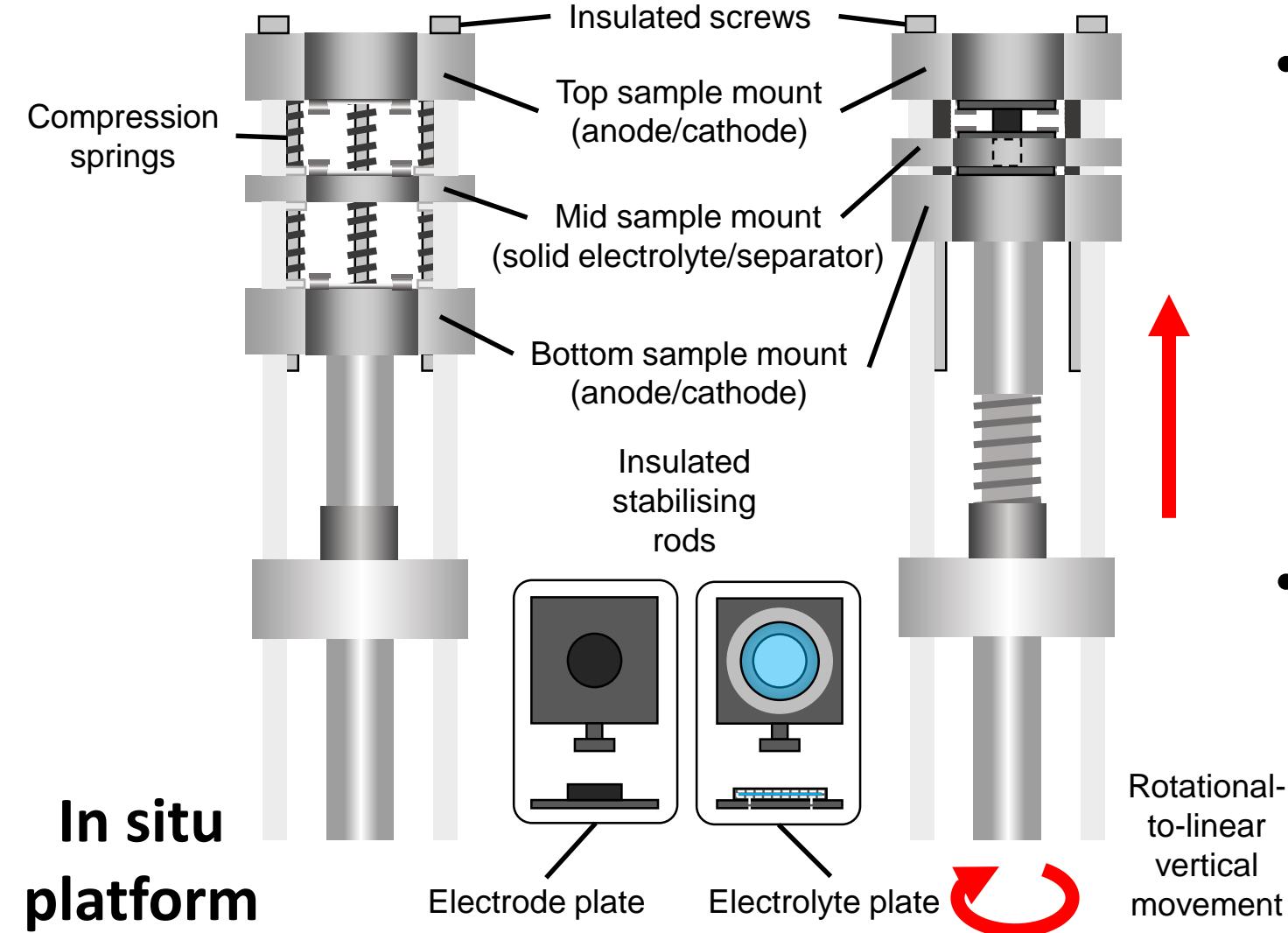
- Develop new in situ and operando platforms that will enable characterisation of buried interfaces in working batteries
- **PI:** Prof Robert Weatherup (Oxford)
- **Co-Is:** Dr Alex Walton (Manchester), Prof Rob Dryfe (Manchester), Dr Nicholas Lockyer (Manchester), Prof Wendy Flavell (Manchester), Prof Martin Castell (Oxford), Dr Tien-Lin Lee (Diamond)



The University of Manchester



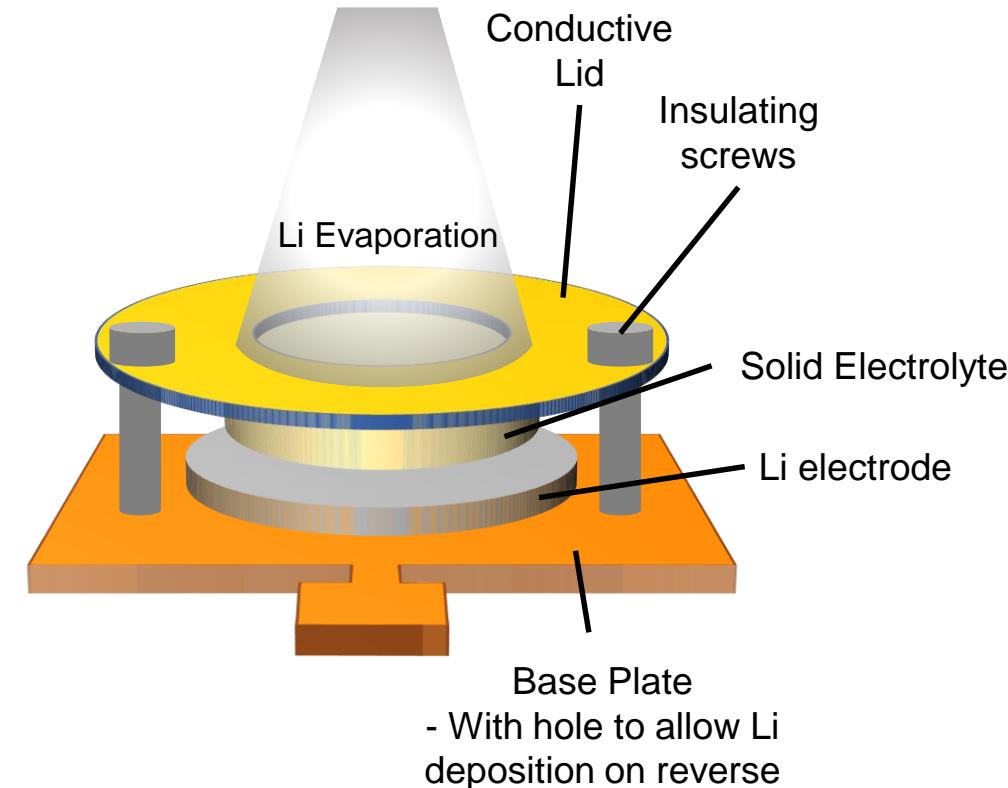
What Lies Beneath? In situ and operando characterisation of battery materials



- **In situ platform:** aiming to assemble/disassemble/reassemble battery components (anode, cathode and solid electrolyte/separator) at various states of charge under high vacuum conditions
- Can then transport components to characterisation equipment (HAXPES, NEXAFS, SIMS, SEM)

What Lies Beneath? In situ and operando characterisation of battery materials

- **Operando platform:** aiming to directly measure battery interfaces during cycling
- Deposition of Li metal onto solid electrolyte to make symmetric cell (Li/solid electrolyte/Li)
- Cycle under high vacuum conditions and measure interface simultaneously

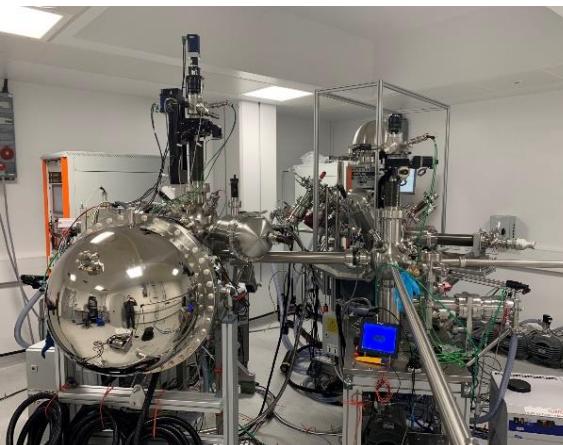
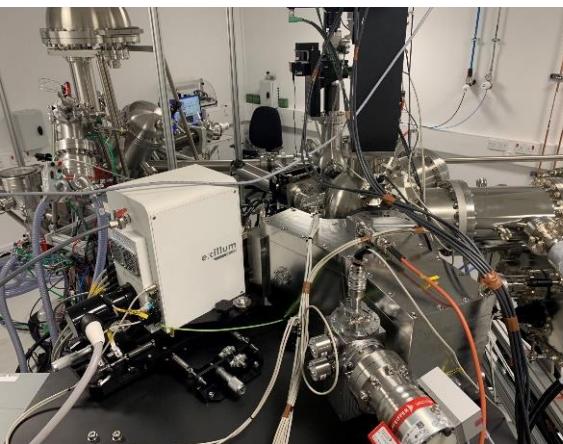


Operando platform

HAXPES benefits

“XPS on steroids”

1. Deeper core levels for larger atoms (Si+) – high sensitivity factors (sometimes >100 x sensitivity of C)
2. Deeper core levels – multiple depths using different KE electrons
3. Extension of sampling depth up to ~ 50 nm using core levels, potentially hundreds of nm using inelastic background
4. Angle-resolved mode for non-destructive depth profiling from the surface into the bulk (XPS can then be used as a surface reference measurement)
5. Expect a rise in application of HAXPES now viable measurements enabled in the lab (not just triage experiments ahead of SR time, lab environment allows fast design/implementation of sample preparation/ in situ/ operando schemes)



Royce.ac.uk



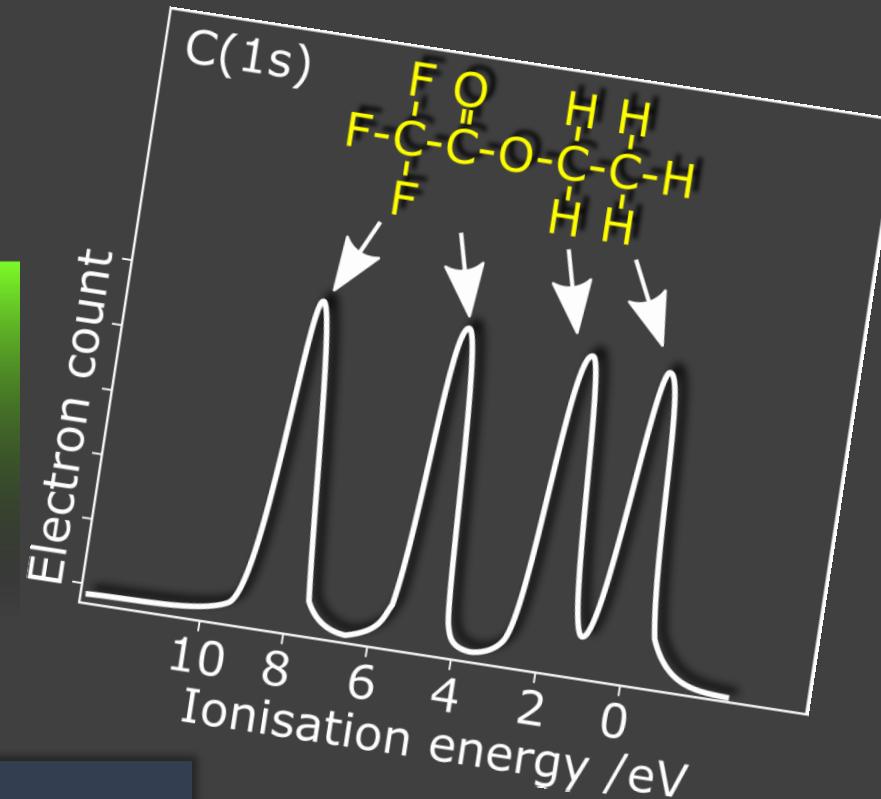
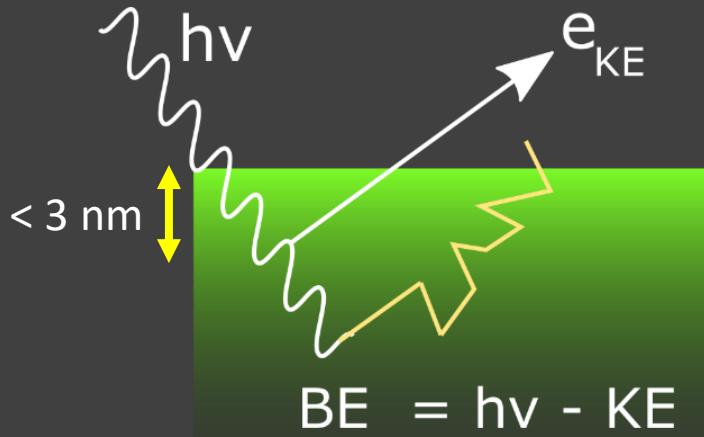
HarwellXPS

EPSRC National XPS Research Facility

www.harwellxps.uk
 @harwellxps



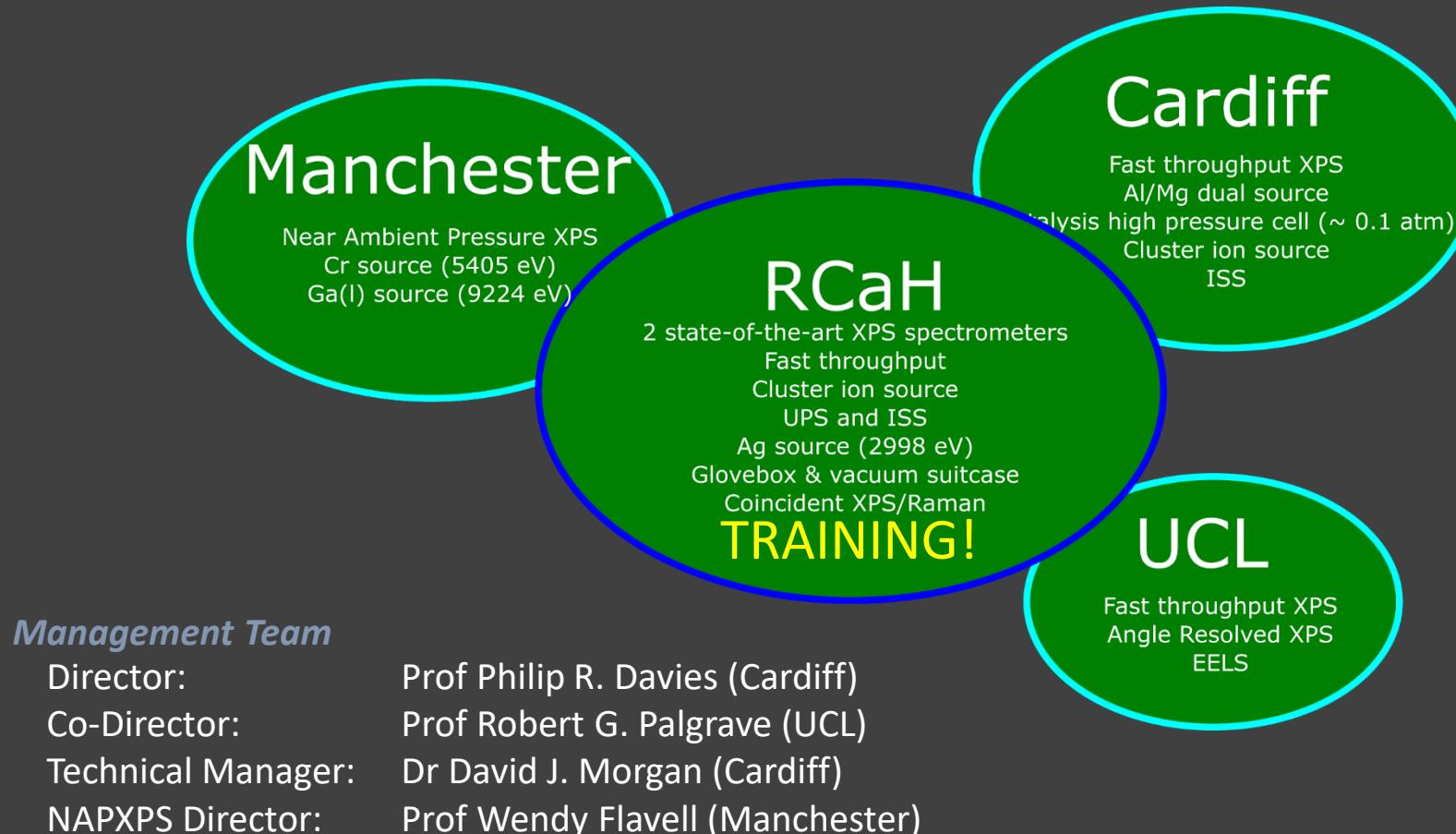
X-Ray Photoelectron Spectroscopy



X-Ray Photoelectron Spectroscopy

- Surface sensitive
- Elemental and chemical sensitivity
- Quantitative

HarwellXPS hub & spoke structure



RCaH Hub

Research Officers: Dr Mark Isaacs & Dr Shaoliang Guan

Manchester Hub

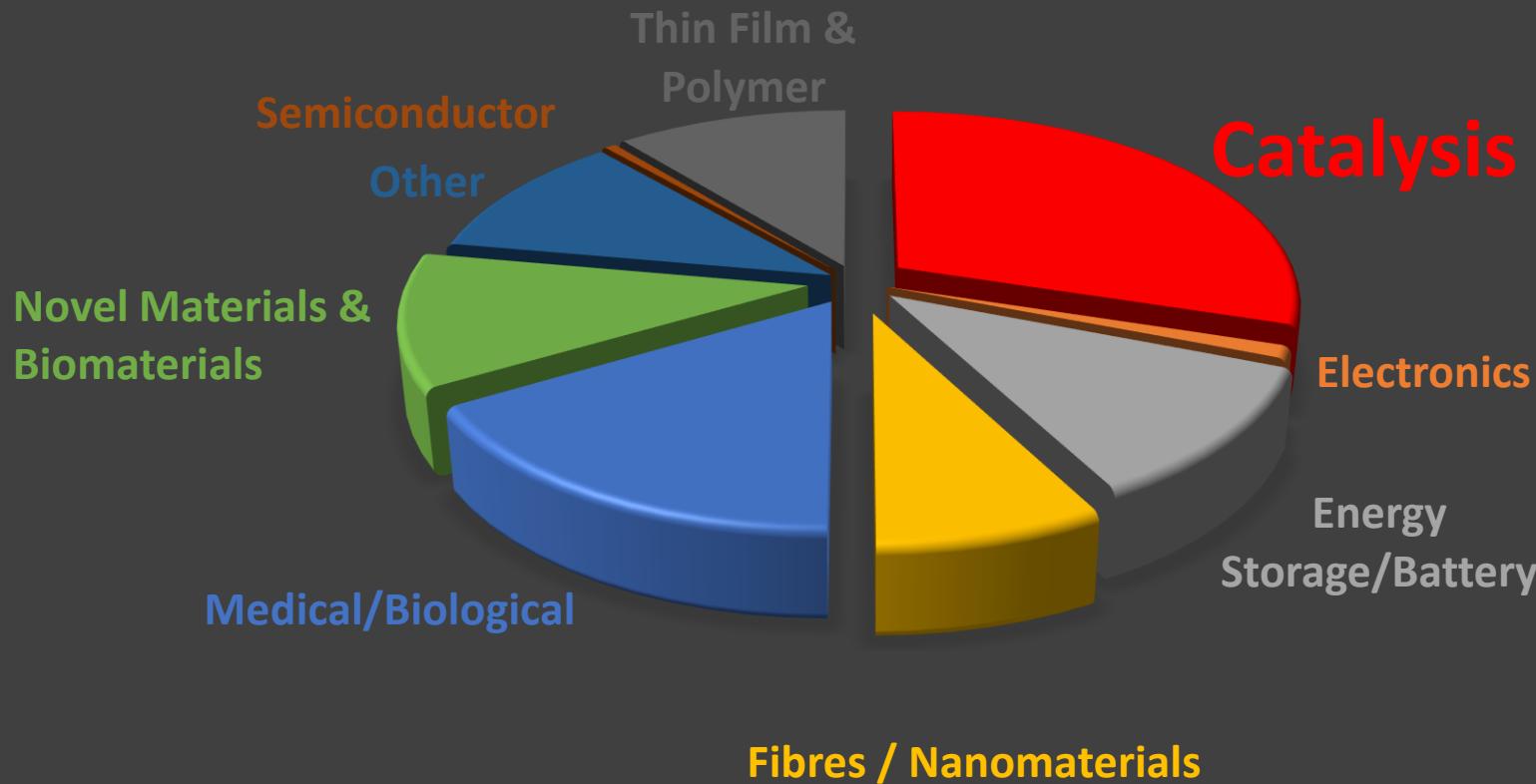
Research Officers: Dr Alex Walton & Dr Ben Spencer

Training

XPS analysis looks easy, *its not!*
Avoid mistakes, get trained by the experts

Training days	Date	Where
Harwell XPS Training Day 1 (Beginners)	15/11/2019	Harwell
<i>TWO Day Training (Beginners & Intermediate)</i>	<i>14th & 15th April 2020</i>	<i>SCI offices London</i>
<i>THREE Day Training (Intermediate & Advanced)</i>	<i>Sept 2020</i>	<i>Cardiff</i>
Annual conference	10/6/2019	Harwell
Faraday Discussion Meeting	April 2022	London

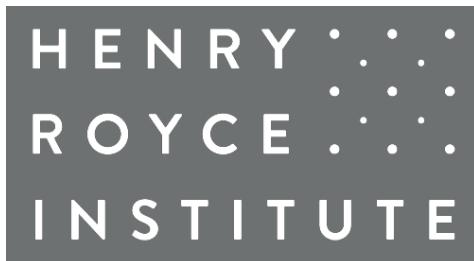
Samples by research area



67.5 % of samples analysed within 1 day

93.8 % of samples analysed within 1 week

www.uksaf.net



New technologies and advancements in Surface Analysis

**Summer meeting 8-9 July 2020
Henry Royce Institute Hub, Manchester**

For more info please contact me at
ben.spencer@manchester.ac.uk

Tues 7 th July	– QUASES workshop with Sven Tougaard
Weds 8 th July	– Conference dinner
Thursday 9 th July	– Tour of the facilities
Friday 10 th July	– CASAXPS training with Neil Fairley

Acknowledgements



Wendy Flavell (academic lead)
Chris Muryn
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Suresh Maniyarasu



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David Cant
Ben Reed
Magdalena Wywias



Elizabeth Gardner
Helen Ryder
Julia Lawson
Cath Davies
Dan Lake

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Sven Tougaard



Susanna Eriksson
Ad Ettema
Shoresh Soltani
Manfred Maschek
Tomas Weill



Tien-Lin Lee
Pardeep Kumar Thakur

... and thank you for your attention!